

## Thermally induced phase transition in $\text{Sn}_x\text{S}_y$ thin films

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Presently, the earth-abundant and non-toxic  $\text{SnS}_2$  and  $\text{SnS}$  compounds could be considered as the promising optoelectronic material. This is due the fact that  $\text{SnS}_2$  has n-type conductivity, high carrier mobility and wide band gap of 2.2 eV. These properties make it possible to use  $\text{SnS}_2$  as a window layer in solar cells. Whereas  $\text{SnS}$  has p-type conductivity, high absorption coefficient and band gap of about 1.3 eV is suitable material for absorber layer in thin film solar cells. Also opposite conductivity of  $\text{SnS}$  and  $\text{SnS}_2$  gives an opportunity to create n -  $\text{SnS}_2$ /p -  $\text{SnS}$  heterojunction.

$\text{SnS}_2$  films were obtained by the close-spaced vacuum sublimation method. SEM images of the surface and cross-section of the obtained samples shows that films consist of plate-like crystallites with average grain size of 2  $\mu\text{m}$ . Thickness of the films was 4  $\mu\text{m}$ . The annealing of the samples was carried out at 300, 400 and 500  $^\circ\text{C}$  for 30, 60 and 90 min for each of temperatures in vacuum. In order to study phase composition of the  $\text{Sn}_x\text{S}_y$  films XRD and Raman spectroscopy were used. It was determined that annealing in vacuum of  $\text{SnS}_2$  films at 500  $^\circ\text{C}$  for 90 min leads to the formation of single phase  $\text{SnS}$ . While, the smaller time and temperature of annealing leads to the mixed phase composition of  $\text{SnS}$ ,  $\text{Sn}_2\text{S}_3$  and  $\text{SnS}_2$ . Annealing at 500 C for 90 min lead to the porous structure of the material. EDS analysis shows that the non-annealed films has typical for  $\text{SnS}_2$  value of Sn:S ratio of 0.49 . Annealing at higher temperature of 500  $^\circ\text{C}$  for 90 min shows that films have Sn:S ratio of 0.96. That is close to stoichiometric composition of  $\text{SnS}$  compound. These results confirm the XRD and Raman data indicating that annealing at 500  $^\circ\text{C}$  for 90 min lead to phase transition from hexagonal  $\text{SnS}_2$  to orthorhombic  $\text{SnS}$ .

### Бібліографічний опис

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